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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω) TYP.	I _D (A)	Q _g (TYP.)			
100	1.3 at V _{GS} = 10 V	300	183 nC			

FEATURES

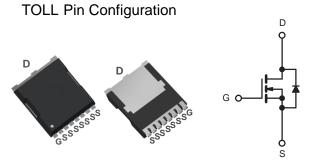
• DT-Trench Power MOSFET

- Uninterruptible power supplies

- AC/DC switch-mode power supplies

• 100 % R_g and UIS tested

HALOGEN **FREE**



N-Channel MOSFET

- Lighting • Synchronous rectification
- DC/DC converter

APPLICATIONS • Power supplies:

- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	100	V			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current /T 150 °C)	T _C = 25 °C	,	300			
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	I _D	195			
Pulsed Drain Current (t = 100 μs)	I _{DM}	1200	A			
Avalanche Current	L = 0.1 mH	I _{AS}	88			
Single Avalanche Energy ^a	L=0.1 IIIH	E _{AS}	3090	mJ		
Maniana Danian Disaination 9	T _C = 25 °C	P _D	480 b	W		
Maximum Power Dissipation ^a	T _C = 100 °C	TD T	3.9 b	VV		
Operating Junction and Storage Temperature F	T _J , T _{stg}	-55 to +150	°C			

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	LIMIT	UNIT				
Junction-to-Ambient (PCB Mount) ^c	t ≤ 10 s	R _{thJA}	12	°C // //			
Junction-to-Case (Drain)	Steady State	R _{thJC}	0.26	°C/W			

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

Rev. 1.0



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SPECIFICATIONS ($T_J = 25 ^{\circ}C$,	unless othe	erwise noted)				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	=	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	=	=	± 100	nA
		V _{DS} = 100 V, V _{GS} = 0 V -		-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V, T _J = 85 °C	-	-	30	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	300	-	=	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	1.3	1.6	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 3 A	-	21	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	11080	-	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	3030	-	
Reverse Transfer Capacitance	C _{rss}		-	42	-	
Total Gate Charge ^c	Q_g		-	179	-	nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 100 \text{ A}$	-	45	-	
Gate-Drain Charge ^c	Q_{gd}		-	51	-	
Gate Resistance	R_g	f = 1 MHz	1	2.0	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	42	-	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, I_D = 100 \text{ A}, R_g = 6\Omega$	-	57	-	ns
Turn-Off Delay Time °	t _{d(off)}	V _{GEN} = 10 V	-	45	-	
Fall Time ^c	t _f		-	77	-	
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)				
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	300	Α
Pulsed Current (t = 100 μs)	I _{SM}		-	-	1200	Α
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1	V
Reverse Recovery Time	t _{rr}	L = 10 A di/dt = 100 A/vs	-	402	-	ns
Reverse Recovery Charge	Q _{rr}	I _F = 10 A, di/dt = 100 A/μs	-	1.6	-	μC

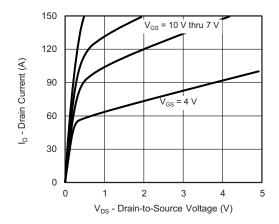
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

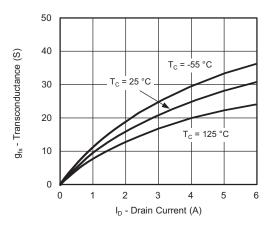
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



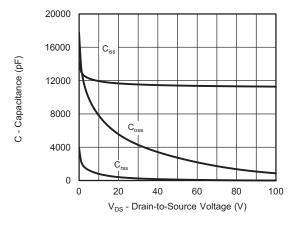
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



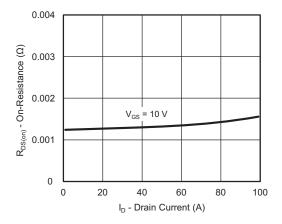
Output Characteristics



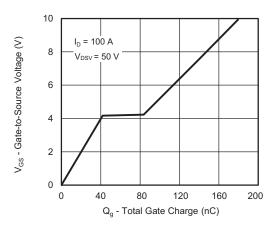
Transconductance



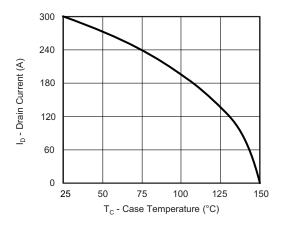
Capacitance



On-Resistance vs. Drain Current



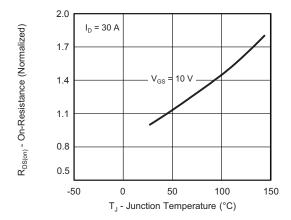
Gate Charge



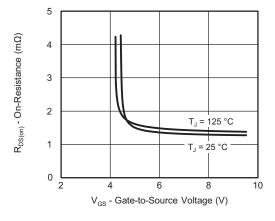
Current De-Rating



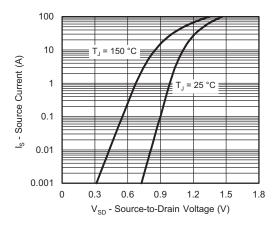
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



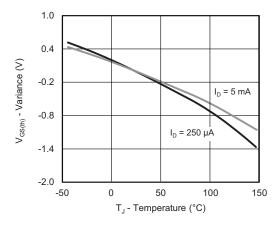
On-Resistance vs. Junction Temperature



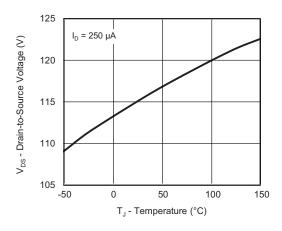
On-Resistance vs. Gate-to-Source Voltage



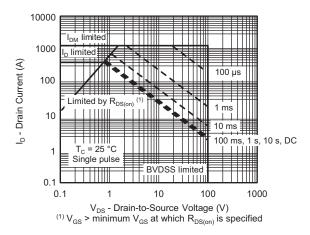
Source Drain Diode Forward Voltage



Threshold Voltage

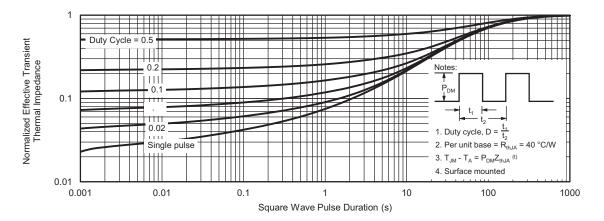


Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

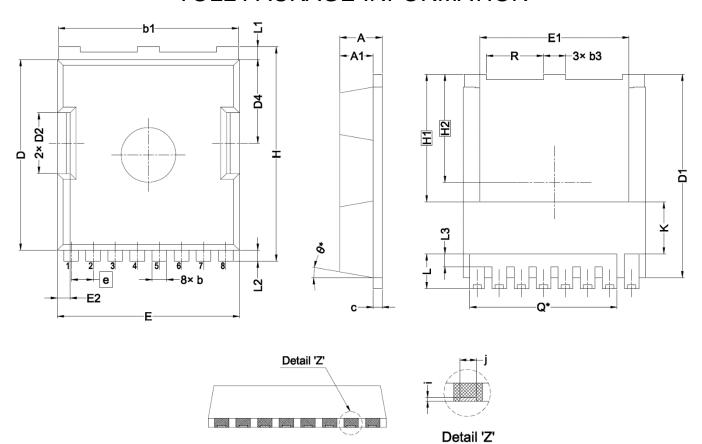
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



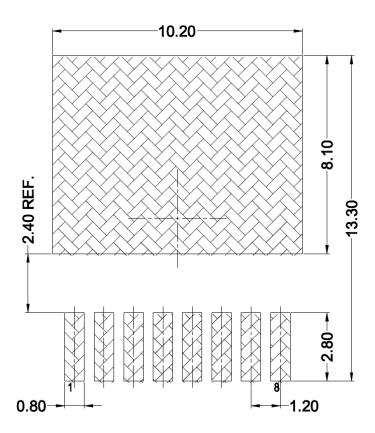
TOLL PACKAGE INFORMATION



CVMDOL		mm		CVMDOL	mm		
SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
Α	2.20	2.30	2.40	Н	11.58	11.68	11.78
A 1	1.70	1.80	1.90	H1	6.95 BSC		
b	0.70	0.80	0.90	H2	5.89 BSC		
b1	9.70	9.80	9.90	i	0.10 REF		
b3	1.10	1.20	1.30	j	0.46 REF		
С	0.40	0.50	0.60	K	2.80 REF		
D	10.28	10.38	10.48	L	1.40	1.90	2.10
D1	10.98	11.08	11.18	L1	0.60	0.70	0.80
D2	3.20	3.30	3.40	L2	0.50	0.60	0.70
D4	4.45	4.55	4.65	L3	0.30	0.70	0.80
E	9.80	9.90	10.00	N	8		
E1	8.00	8.10	8.20	Q	8.00 REF		
E2	0.60	0.70	0.80	R	3.00	3.10	3.20
е	1.20 BSC		θ	10° REF			



TOLL RECOMMENDED LAND PATTERN



unit: mm





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